

ABSTRACT

A sputtering target material, wherein the strength of a sputtering target material can be enhanced without using pure Ta to prevent cracking during sputtering and generating particles and to suppress an irregular composition of a sputtered film, is provided. The present invention provides a sputtering target material containing, in at%, 35% to 50% of Ta with the balance being Ni and an inevitable impurity, wherein the sputtering target is composed only of a Ni_2Ta compound phase and a NiTa compound phase, and a microstructure in each of the Ni_2Ta compound phase and the NiTa compound phase has a maximum inscribed circle diameter of not more than 10 μm .

FIGURE 1